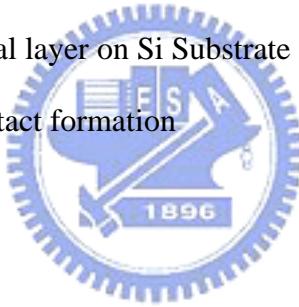


# Contents

<b>Abstract (in Chinese)</b>	i
<b>Abstract (in English)</b>	ii
<b>Acknowledgment (in Chinese)</b>	iii
<b>Figure Captions</b>	vi

## Chapter 1 Introduction

<b>1 General Background and Motivations</b>	1
1-1 Growth of the $\text{Si}_{1-x}\text{Ge}_x$ and Ge epitaxial layers on Si substrate	2
1-2 Growth of the GaAs epitaxial layer on Si Substrate	4
1-3 Growth of the ZnSe epitaxial layer on Si Substrate	5
1-4 Nickel germanosilicide contact formation	6
1-5 Outline of this dissertation	7
1-6 References	9



## Chapter 2 Growth of the SiGe and Ge epitaxial layers on Si substrate

2-1 Introduction	17
2-2 Ge/SiGe epitaxial layer growth procedures	18
2-3 Characteristics of the SiGe and Ge epitaxial layers	19
2-4 Conclusions	21
2-5 References	23

## Chapter 3 Growth of the device-quality GaAs epitaxial layers on Si substrates

3-1 Introduction	36
3-2 GaAs epitaxial layer growth procedures	38
3-3 Material characteristics of the GaAs epilayer on the off-cut Ge/GeSi/Si	39
3-4 Analysis of Ge inter-diffusion in $\text{GaAs}/\text{Ge}/\text{Ge}_{0.95}\text{Si}_{0.05}/\text{Ge}_{0.9}\text{Si}_{0.1}/\text{Si}$	42

3-5 Conclusions	43
-----------------	----

3-6 References	44
----------------	----

## **Chapter 4 Growth of ZnSe epilayer on Si substrate using Ge/Ge<sub>x</sub>Si<sub>1-x</sub> buffer structure**

4.1 Introduction	60
------------------	----

4-2 ZnSe epitaxial layer growth procedures	62
--	----

4-3 Analysis of Ge inter-diffusion in ZnSe/Ge/Ge <sub>0.95</sub> Si <sub>0.05</sub> /Ge <sub>0.9</sub> Si <sub>0.1</sub> /Si	62
--	----

4-4 Optical characteristics of the ZnSe epilayers grown on Ge/GeSi/Si system	63
--	----

4-5 Material characteristics of the ZnSe epilayers grown on Ge/GeSi/Si system	64
---	----

4-6 Suppression of DLE formation using the method of low temperature MEE and buffer layer growth with <i>in-situ</i> annealing	65
---	----

4-7 Conclusions	66
-----------------	----

4-8 References	68
----------------	----

## **Chapter 5 Nickel silicide and nickel germanosilicide based Ohmic contacts on Si<sub>1-x</sub>Ge<sub>x</sub>**



5-1 Introduction	79
------------------	----

5-2 Experimental procedures	81
-----------------------------	----

5-3 Material properties of the Ni/Si <sub>1-x</sub> Ge <sub>x</sub> thin films	82
--	----

5-4 Electrical property of Ni/Si <sub>1-x</sub> Ge <sub>x</sub> thin films	84
--	----

5-5 Material and electrical properties of Ni/Si/Si <sub>1-x</sub> Ge <sub>x</sub> Ohmic contacts	85
--	----

5-6 Morphological stability of Ni/Si/Si <sub>1-x</sub> Ge <sub>x</sub> thin films	87
---	----

5-7 Conclusions	90
-----------------	----

5-8 References	92
----------------	----

<b>Chapter 6 Conclusions</b>	123
------------------------------	-----